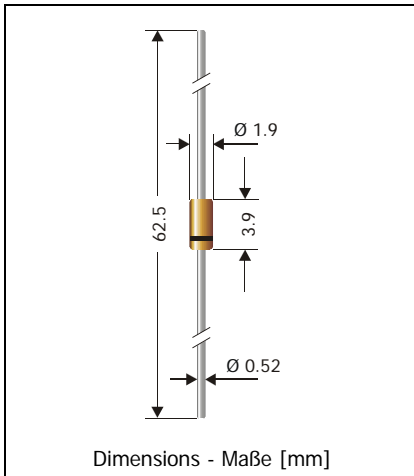


SD103A ... SD103C

Si-Schottky-Barrier Diodes
Si-Schottky-Barrier Dioden

Version 2005-06-21



| | |
|--|-------------------|
| Nominal current Nennstrom | 0.2 A |
| Repetitive peak reverse voltage Periodische Spitzensperrspannung | 20...40 V |
| Glass case Glasgehäuse | DO-35 (SOD-27) |
| Weight approx. Gewicht ca. | 0.13 g |
| Equivalent SMD-version Äquivalente SMD-Ausführung | LL103C...LL103A |
| Standard packaging taped in ammo pack Standard Lieferform gegurtet in Ammo-Pack | |

Maximum ratings ($T_A = 25^\circ\text{C}$)Grenzwerte ($T_A = 25^\circ\text{C}$)

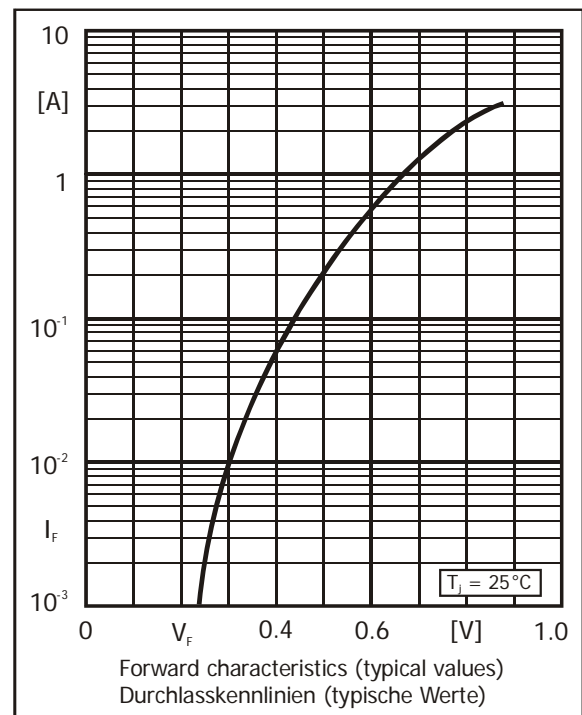
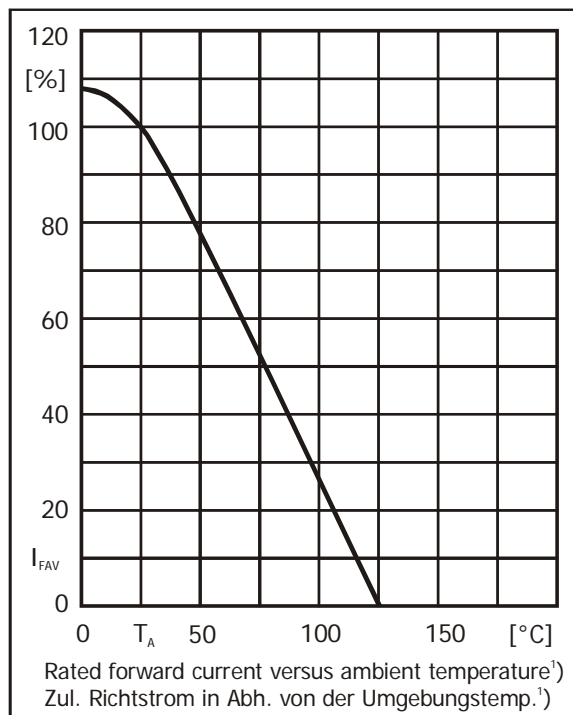
| Type Typ | Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] | Forward voltage Durchlass-Spannung V_F [V] | |
|-------------|--|--|-----------------------|
| | | $I_F = 20\text{ mA}$ | $I_F = 200\text{ mA}$ |
| SD103C | 20 | < 0.37 | < 0.6 |
| SD103B | 30 | < 0.37 | < 0.6 |
| SD103A | 40 | < 0.37 | < 0.6 |

| | | | |
|---|--------------------------|----------------|------------------------------|
| Power dissipation Verlustleistung | $T_A = 25^\circ\text{C}$ | P_{tot} | 400 mW ¹⁾ |
| Peak forward surge current, 60 Hz half sine-wave Stoßstrom für eine 60 Hz Sinus-Halbwellen | | I_{FSM} | 15 A |
| Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur | | T_j T_s | -50...+125°C -50...+175°C |

1 Valid, if leads are kept at ambient temperature at a distance of 5 mm from case
Gültig, wenn die Anschlussdrähte in 5 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

Characteristics ($T_j = 25^\circ\text{C}$)
Kennwerte ($T_j = 25^\circ\text{C}$)

| | | | |
|---|--|------------------|-----------------------|
| Leakage current Sperrstrom | SD103C $V_R = 10\text{ V}$ SD103B $V_R = 20\text{ V}$ SD103A $V_R = 30\text{ V}$ | I_R | $< 5\ \mu\text{A}$ |
| Max. junction capacitance Max. Sperrschichtkapazität | $V_R = 0\text{ V}, f = 1\text{ MHz}$ | C_{tot} | typ. 50 pF |
| Reverse recovery time Sperrverzug | $I_F = 200\text{ mA}$ through/über $I_R = 200\text{ mA}$ to $I_R = 20\text{ mA}$ | t_{rr} | typ. 10 ns |
| Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft | | R_{thA} | $< 250\text{ K/W}^1)$ |



1 Valid, if leads are kept at ambient temperature at a distance of 5 mm from case
Gültig, wenn die Anschlussdrähte in 5 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden